

1.1 Features

- $V_{DS}=60V$
- $I_D=300mA$
- $R_{DS(ON)}<3\Omega(V_{GS}=10V)$
- $R_{DS(ON)}<4\Omega(V_{GS}=5V)$

1.2 Features

- High density cell design for low $R_{DS(ON)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

2. Application

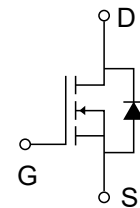
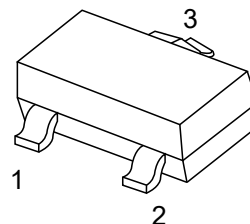
- Load Switch for Portable Devices

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3. Pinning information

Pin	Symbol	Description
1	G	GATE
2	S	SOURCE
3	D	DRAIN

SOT-23



4. Absolute Maximum Ratings $T_A = 25^\circ C$

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	300	mA
Power Dissipation	P_D	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~+150	$^\circ C$



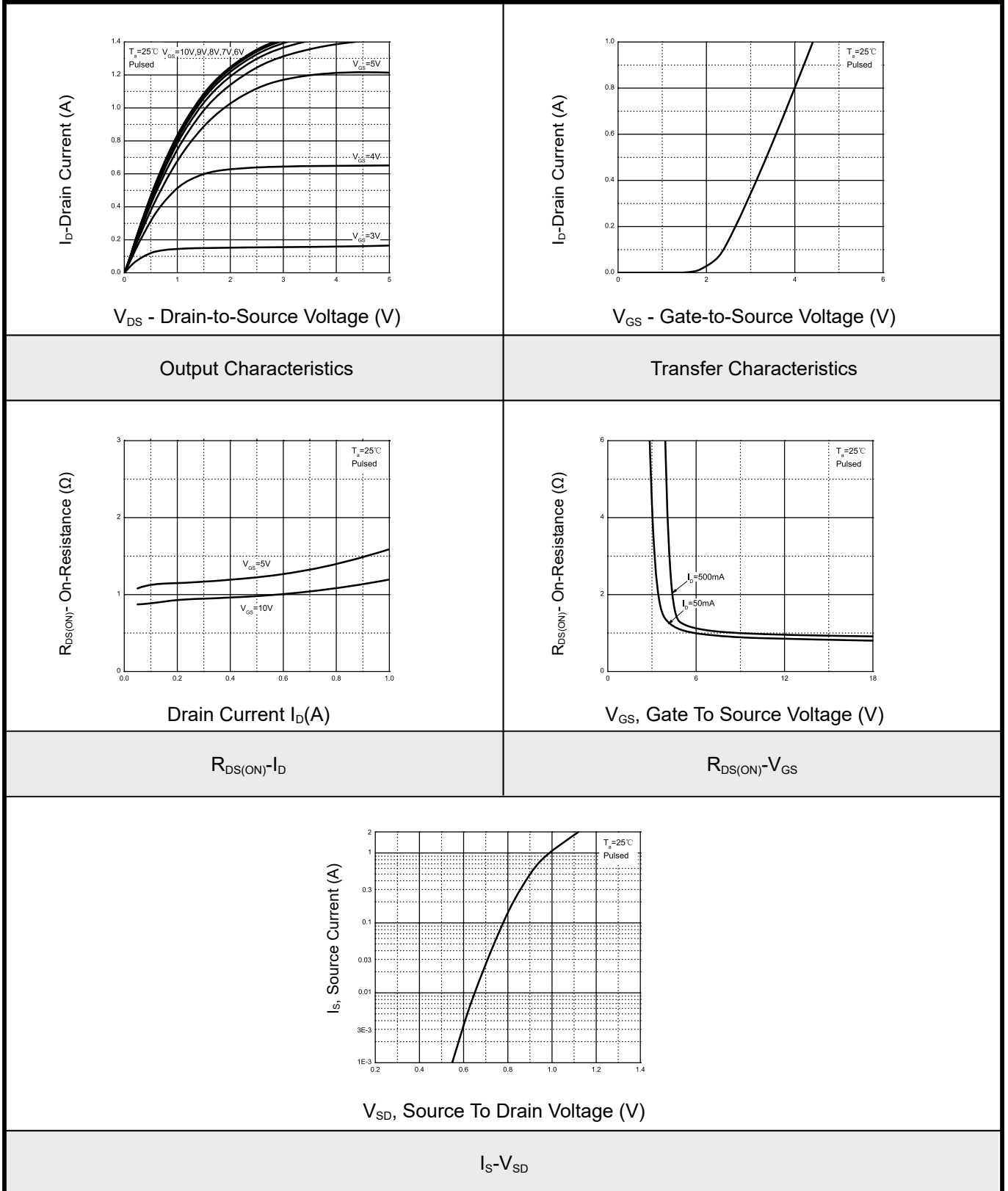
5. Electrical Characteristics $T_A = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1		2.5	V
Gate-body Leakage	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 10\text{V}$			± 80	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{V}, V_{GS}=0\text{V}$			80	nA
On-state Drain Current	$I_{D(ON)}$	$V_{DS}=7\text{V}, V_{GS}=10\text{V}$			500	mA
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=300\text{mA}$			3	Ω
		$V_{GS}=5\text{V}, I_D=150\text{mA}$			4	Ω
Forward Trans conductance	g_{FS}	$V_{DS}=10\text{V}, I_D=200\text{mA}$	80			ms
Drain-source on-voltage	$V_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$			3.75	V
		$V_{GS}=5\text{V}, I_D=50\text{mA}$			0.375	V
Diode Forward Voltage	V_{SD}	$I_S=115\text{mA}, V_{GS}=0\text{V}$	0.55		1.2	V
Input Capacitance *	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$			50	pF
Output Capacitance *	C_{oss}				25	pF
Reverse Transfer Capacitance *	C_{rss}				5	pF
SWITCHING TIME						
Turn-on Time *	$t_{D(on)}$	$V_{DD}=25\text{V}, R_L=50\Omega, R_G=25\Omega$			20	ns
Turn-off Time *	$t_{D(off)}$	$I_D=500\text{mA}, V_{GEN}=10\text{V}$			40	ns

*These parameters have no way to verify.

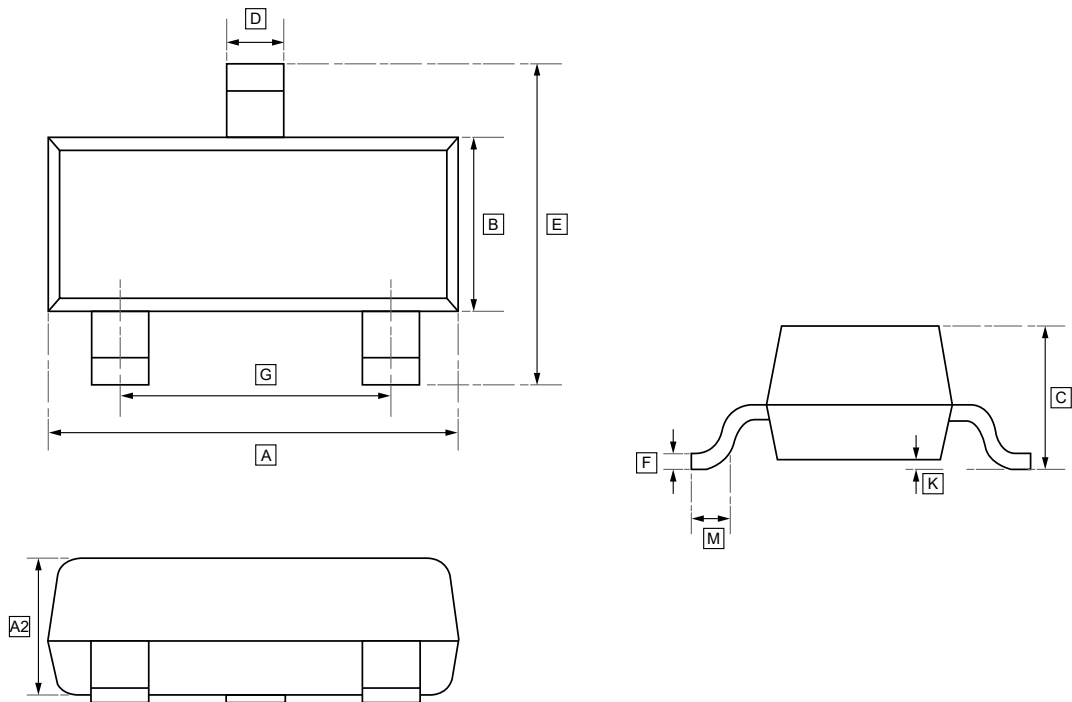


6. Typical Characteristics





7.SOT-23 Package Outline Dimensions

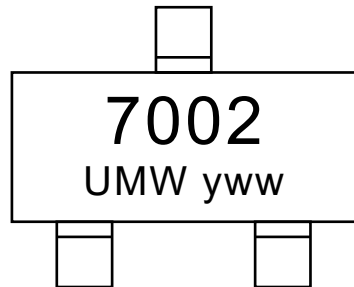


DIMENSIONS (mm are the original dimensions)

Symbol	A	B	C	D	E	G	K	M	A2	F
Min	2.85	1.20	0.90	0.40	2.25	1.80	0.00	0.30	0.95	0.095
Max	3.04	1.40	1.10	0.50	2.55	2.00	0.10	-	1.05	0.115



8. Ordering Information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW 2N7002	SOT-23	3000	Tape and reel



9.Disclaimer

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